

# HiPerFRED

$V_{RRM}$  = 1200 V  
 $I_{FAV}$  = 2x 15 A  
 $t_{rr}$  = 40 ns

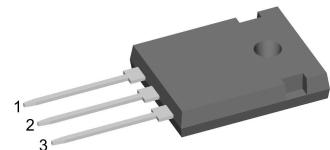
High Performance Fast Recovery Diode

Low Loss and Soft Recovery

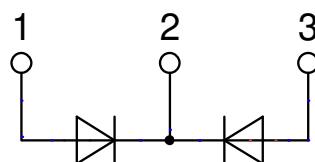
Common Cathode

Part number

**DSEC30-12A**



Backside: cathode



## Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low  $I_{rm}$ -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{rm}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

## Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

## Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

## Disclaimer Notice

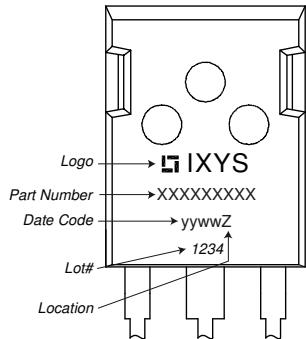
Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).

**Fast Diode**

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
$V_{RSM}$	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1200	V
$V_{RRM}$	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1200	V
$I_R$	reverse current, drain current	$V_R = 1200 \text{ V}$ $V_R = 1200 \text{ V}$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		100 0,5	$\mu A$ mA
$V_F$	forward voltage drop	$I_F = 15 \text{ A}$ $I_F = 30 \text{ A}$ $I_F = 15 \text{ A}$ $I_F = 30 \text{ A}$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		2,61 3,17 1,86 2,54	V V
$I_{FAV}$	average forward current	$T_C = 120^\circ C$ rectangular $d = 0.5$	$T_{VJ} = 175^\circ C$		15	A
$V_{F0}$ $r_F$	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 175^\circ C$		1,03 46	V $m\Omega$
$R_{thJC}$	thermal resistance junction to case				1,6	K/W
$R_{thCH}$	thermal resistance case to heatsink			0,25		K/W
$P_{tot}$	total power dissipation		$T_C = 25^\circ C$		95	W
$I_{FSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}; V_R = 0 \text{ V}$	$T_{VJ} = 45^\circ C$		90	A
$C_J$	junction capacitance	$V_R = 600 \text{ V}$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$	5		pF
$I_{RM}$	max. reverse recovery current		$T_{VJ} = 25^\circ C$ $T_{VJ} = 100^\circ C$	6 9		A
$t_{rr}$	reverse recovery time	$I_F = 15 \text{ A}; V_R = 600 \text{ V}$ $-di_F/dt = 200 \text{ A}/\mu s$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 100^\circ C$	50 140		ns ns

**Package TO-247**

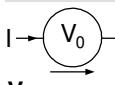
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	<i>RMS current</i>	per terminal <sup>1)</sup>			50	A
$T_{VJ}$	<i>virtual junction temperature</i>		-55		175	°C
$T_{op}$	<i>operation temperature</i>		-55		150	°C
$T_{stg}$	<i>storage temperature</i>		-55		150	°C
<b>Weight</b>				6		g
$M_D$	<i>mounting torque</i>		0,8		1,2	Nm
$F_c$	<i>mounting force with clip</i>		20		120	N

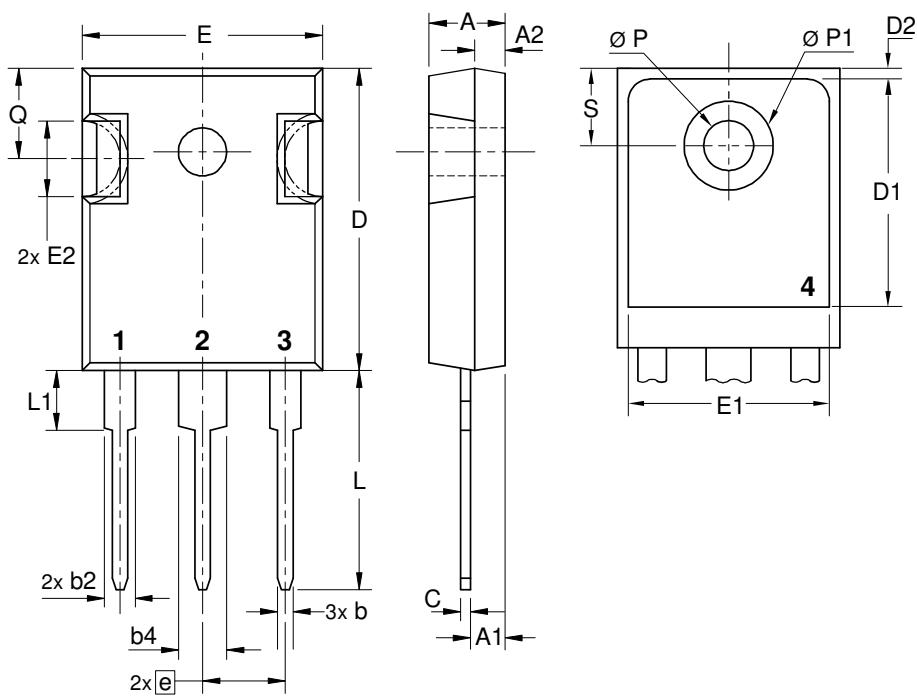
**Product Marking**


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEC30-12A	DSEC30-12A	Tube	30	477117

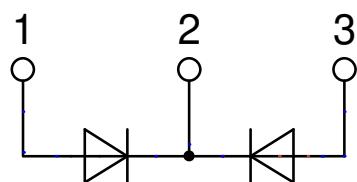
**Equivalent Circuits for Simulation**
<sup>\*</sup>on die level

 $T_{VJ} = 175^\circ\text{C}$ 

	$V_0$	$R_0$	Fast Diode	
$V_{0\ max}$	threshold voltage	1,03		V
$R_{0\ max}$	slope resistance *	43		$\text{m}\Omega$

**Outlines TO-247**


Sym.	Inches min. max.	Millimeter min. max.
A	0.185 0.209	4.70 5.30
A1	0.087 0.102	2.21 2.59
A2	0.059 0.098	1.50 2.49
D	0.819 0.845	20.79 21.45
E	0.610 0.640	15.48 16.24
E2	0.170 0.216	4.31 5.48
e	0.215 BSC	5.46 BSC
L	0.780 0.800	19.80 20.30
L1	- 0.177	- 4.49
Ø P	0.140 0.144	3.55 3.65
Q	0.212 0.244	5.38 6.19
S	0.242 BSC	6.14 BSC
b	0.039 0.055	0.99 1.40
b2	0.065 0.094	1.65 2.39
b4	0.102 0.135	2.59 3.43
c	0.015 0.035	0.38 0.89
D1	0.515 -	13.07 -
D2	0.020 0.053	0.51 1.35
E1	0.530 -	13.45 -
Ø P1	- 0.29	- 7.39



### Fast Diode

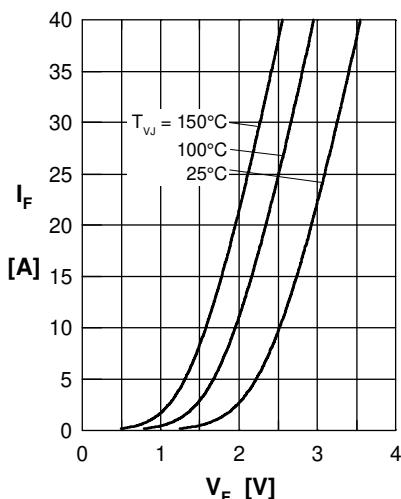


Fig. 1 Forward current  $I_F$  versus  $V_F$

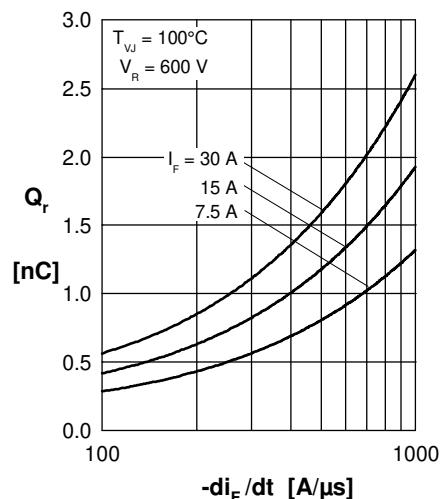


Fig. 2 Typ. reverse recov. charge  $Q_r$  versus  $-di_F/dt$

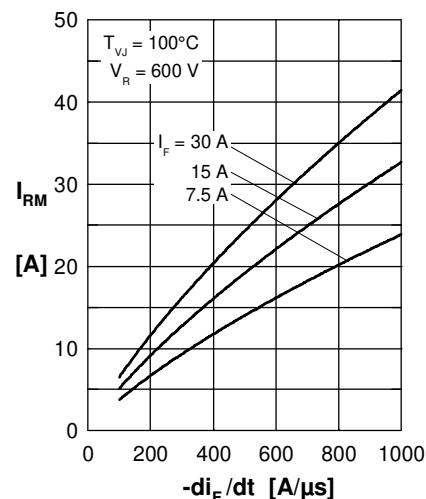


Fig. 3 Typ. peak reverse current  $I_{RM}$  versus  $-di_F/dt$

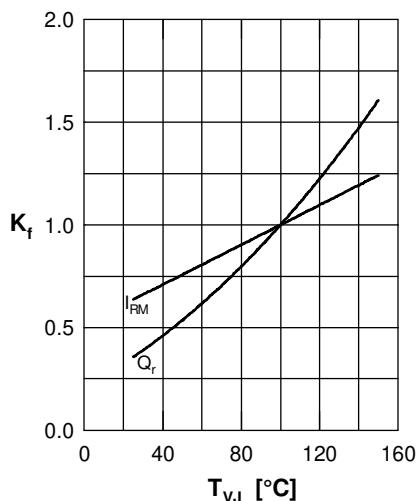


Fig. 4 Typ. dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$

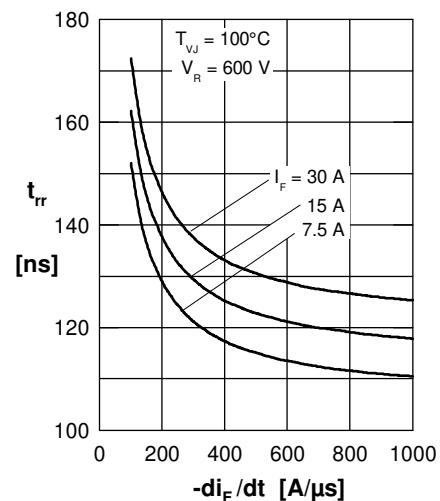


Fig. 5 Typ. recovery time  $t_{rr}$  versus  $-di_F/dt$

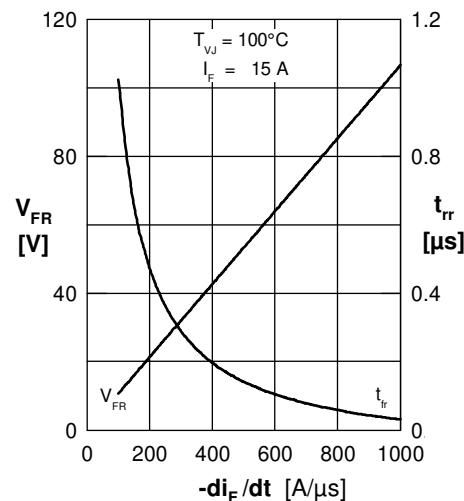


Fig. 6 Typ. peak forward voltage  $V_{FR}$  and  $t_{fr}$  versus  $di_F/dt$

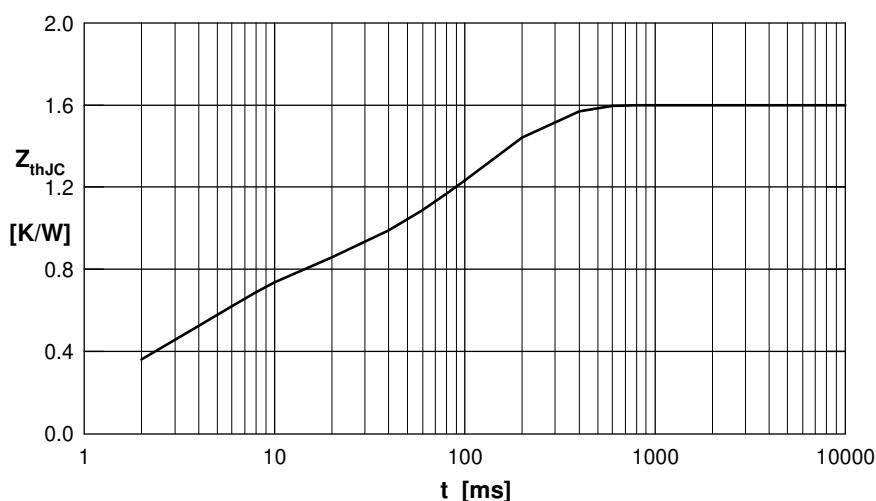


Fig. 7 Transient thermal resistance junction to case  $Z_{thJC}$

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.160	0.0010
2	0.100	0.0150
3	0.500	0.0040
4	0.840	0.1200